IGBT

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

IKP15N65F5

650V DuoPack IGBT and Diode
High speed switching series fifth generation

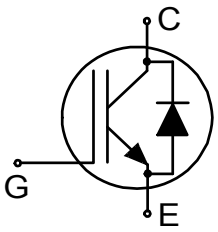
Data sheet

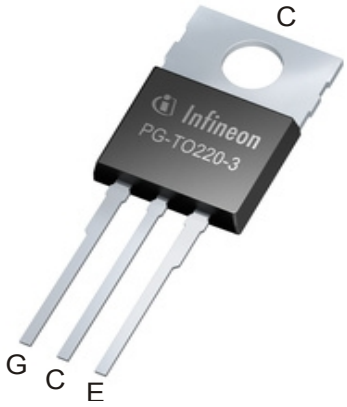
Industrial Power Control

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

Features and Benefits:

High speed F5 technology offering
• Best-in-Class efficiency in hard switching and resonant topologies
• 650V breakdown voltage
• Low gate charge Q_G
• IGBT copacked with RAPID 1 fast and soft antiparallel diode
• Maximum junction temperature 175°C
• Qualified according to JEDEC for target applications
• Pb-free lead plating; RoHS compliant
• Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/





Applications:

• Solar converters
• Uninterruptible power supplies
• Welding converters
• Mid to high range switching frequency converters

Pb-free
Green
Halogen-Free
RoHS

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IKP15N65F5	650V	15A	1.6V	175°C	K15EF5	PG-TO220-3

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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	650	V
DC collector current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_C	 30.0 18.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	45.0	A
Turn off safe operating area $V_{CE} \leq 650V$, $T_{vj} \leq 175°C$	-	45.0	A
Diode forward current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_F	 20.0 12.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	45.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu s$, D < 0.010)	V_{GE}	±20 ±30	V
Power dissipation T_C = 25°C Power dissipation T_C = 100°C	P_{tot}	105.0 52.5	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		1.40	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		2.90	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		62	K/W

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.20mA	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 15.0A T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 175°C	 - - -	 1.60 1.80 1.90	 2.10 - -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 9.0A T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 175°C	 - - -	 1.45 1.40 1.40	 1.80 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.15mA, V_{CE} = V_{GE}	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	 - -	 - -	 40.0 4000.0	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 15.0A	-	22.0	-	S

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	930	-	pF
Output capacitance	C_{oes}		-	24	-	
Reverse transfer capacitance	C_{res}		-	4	-	
Gate charge	Q_G	V_{CC} = 520V, I_C = 15.0A, V_{GE} = 15V	-	38.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 25°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 7.5A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 39.0Ω, $R_{G(off)}$ = 39.0Ω, $L\sigma$ = 30nH, $C\sigma$ = 30pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	17	-	ns
Rise time	t_r		-	7	-	ns
Turn-off delay time	$t_{d(off)}$		-	150	-	ns
Fall time	t_f		-	16	-	ns
Turn-on energy	E_{on}		-	0.13	-	mJ
Turn-off energy	E_{off}		-	0.04	-	mJ
Total switching energy	E_{ts}		-	0.17	-	mJ

Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 2.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 39.0Ω, $R_{G(off)}$ = 39.0Ω, Lσ = 30nH, Cσ = 30pF Lσ, Cσ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	17	-	ns
Rise time	t_r		-	4	-	ns
Turn-off delay time	$t_{d(off)}$		-	190	-	ns
Fall time	t_f		-	10	-	ns
Turn-on energy	E_{on}		-	0.04	-	mJ
Turn-off energy	E_{off}		-	0.02	-	mJ
Total switching energy	E_{ts}		-	0.06	-	mJ

Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 7.5A, di_F/dt = 1000A/µs	-	50	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.19	-	µC
Diode peak reverse recovery current	I_{rrm}		-	8.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-190	-	A/µs

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 2.0A, di_F/dt = 1000A/µs	-	22	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.10	-	µC
Diode peak reverse recovery current	I_{rrm}		-	8.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-620	-	A/µs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 150°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 150°C, V_{CC} = 400V, I_C = 7.5A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 39.0Ω, $R_{G(off)}$ = 39.0Ω, Lσ = 30nH, Cσ = 30pF Lσ, Cσ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	16	-	ns
Rise time	t_r		-	10	-	ns
Turn-off delay time	$t_{d(off)}$		-	190	-	ns
Fall time	t_f		-	5	-	ns
Turn-on energy	E_{on}		-	0.18	-	mJ
Turn-off energy	E_{off}		-	0.06	-	mJ
Total switching energy	E_{ts}		-	0.24	-	mJ

Turn-on delay time	$t_{d(on)}$	T_{vj} = 150°C, V_{CC} = 400V, I_C = 2.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 39.0Ω, $R_{G(off)}$ = 39.0Ω, Lσ = 30nH, Cσ = 30pF Lσ, Cσ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	15	-	ns
Rise time	t_r		-	4	-	ns
Turn-off delay time	$t_{d(off)}$		-	230	-	ns
Fall time	t_f		-	30	-	ns
Turn-on energy	E_{on}		-	0.06	-	mJ
Turn-off energy	E_{off}		-	0.02	-	mJ
Total switching energy	E_{ts}		-	0.08	-	mJ

Diode Characteristic, at T_{vj} = 150°C

Diode reverse recovery time	t_{rr}	T_{vj} = 150°C, V_R = 400V, I_F = 7.5A, di_F/dt = 1000A/µs	-	67	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.39	-	µC
Diode peak reverse recovery current	I_{rrm}		-	9.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-140	-	A/µs

Diode reverse recovery time	t_{rr}	T_{vj} = 150°C, V_R = 400V, I_F = 2.0A, di_F/dt = 1000A/µs	-	35	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.20	-	µC
Diode peak reverse recovery current	I_{rrm}		-	10.2	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-360	-	A/µs

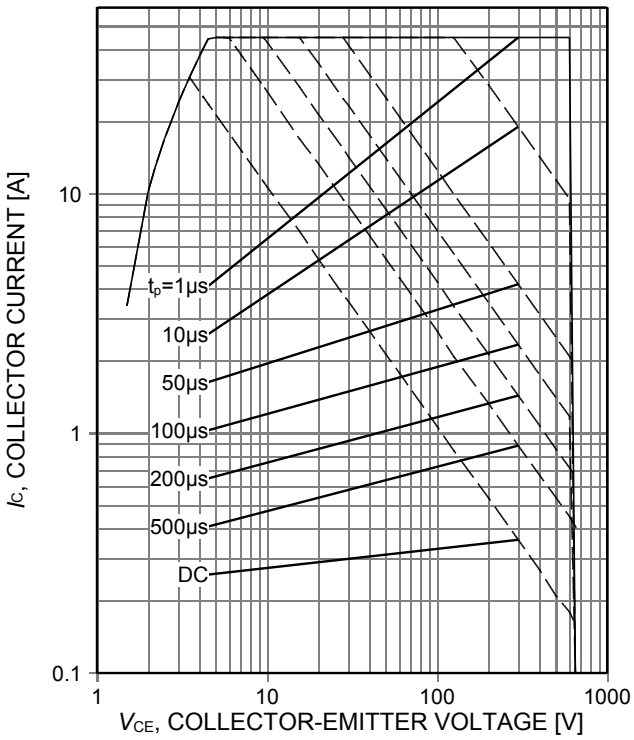


Figure 1. **Forward bias safe operating area**
(D=0, T_C=25°C, T_{vj}≤175°C; V_{GE}=15V.
Recommended use at V_{GE}≥7.5V)

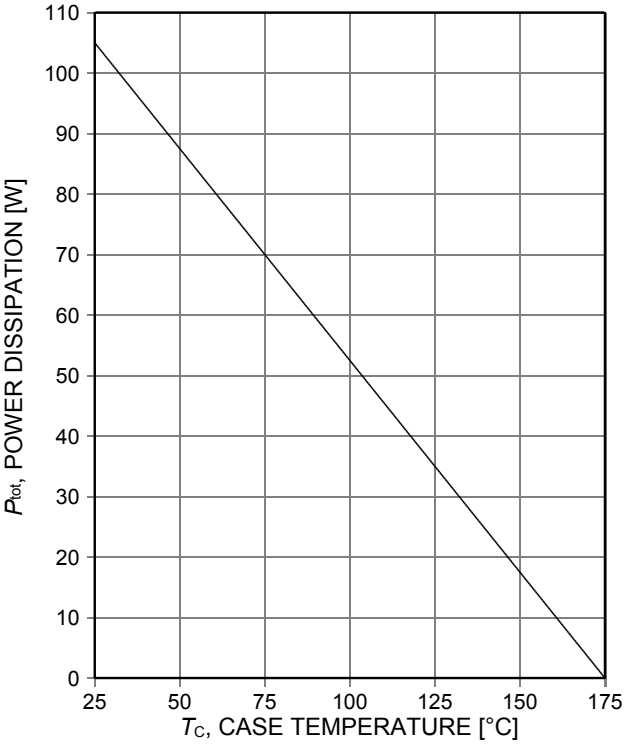


Figure 2. **Power dissipation as a function of case temperature**
(T_{vj}≤175°C)

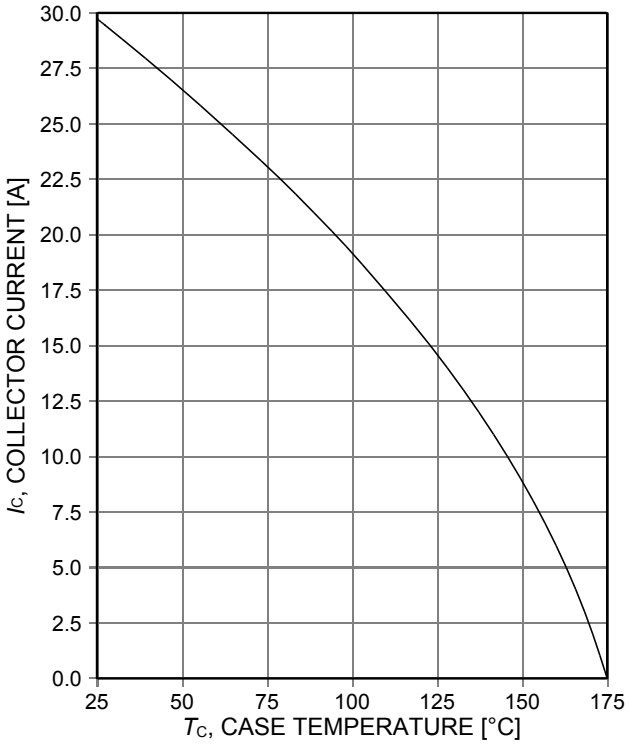


Figure 3. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_{vj}≤175°C)

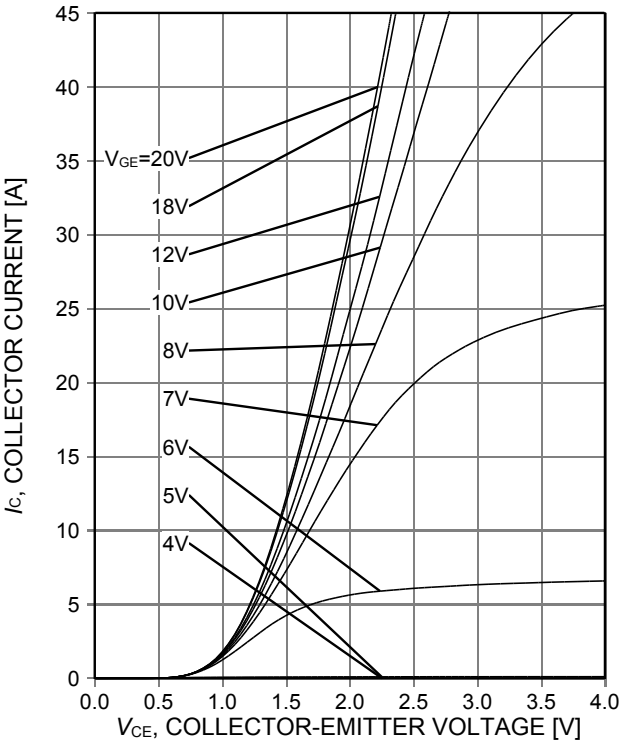


Figure 4. **Typical output characteristic**
(T_{vj}=25°C)

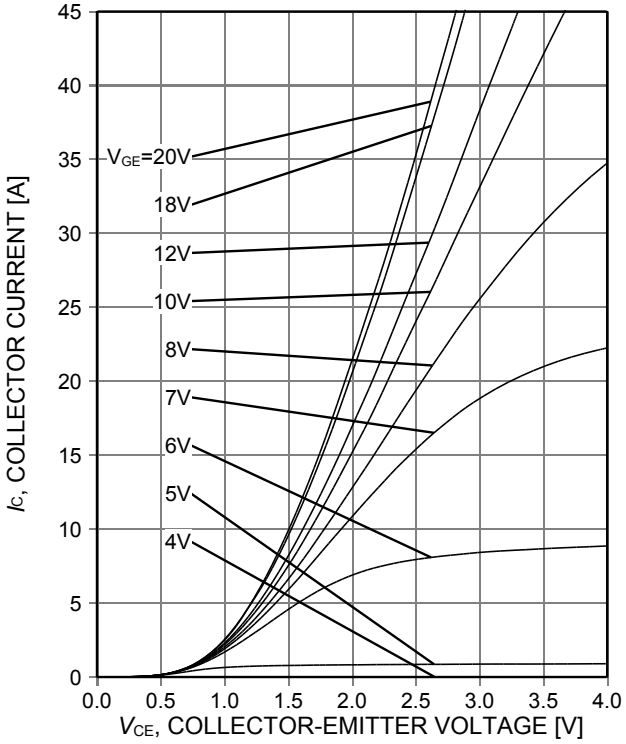


Figure 5. **Typical output characteristic**
(T_{vj}=150°C)

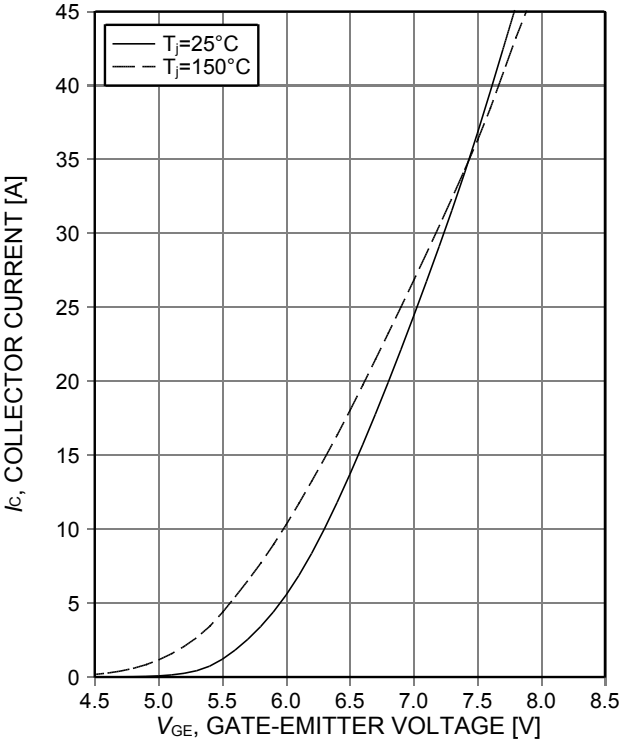


Figure 6. **Typical transfer characteristic**
(V_{CE}=20V)

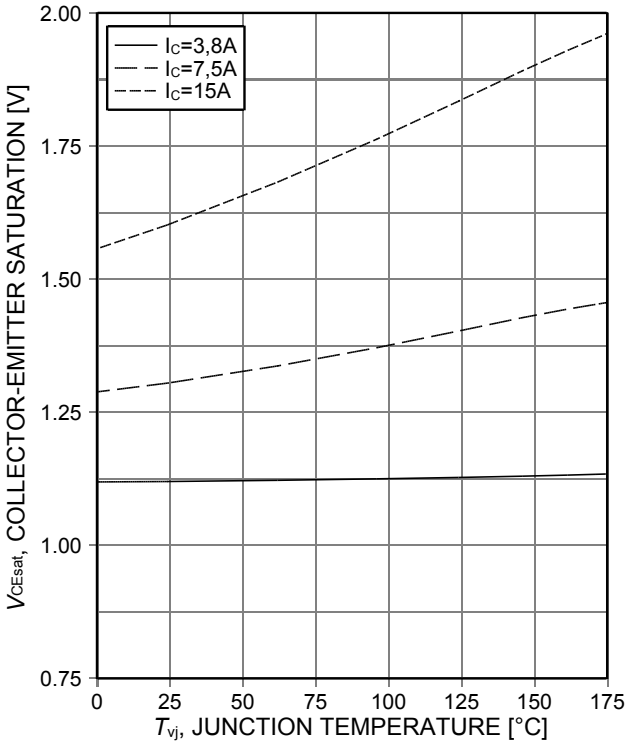


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
(V_{GE}=15V)

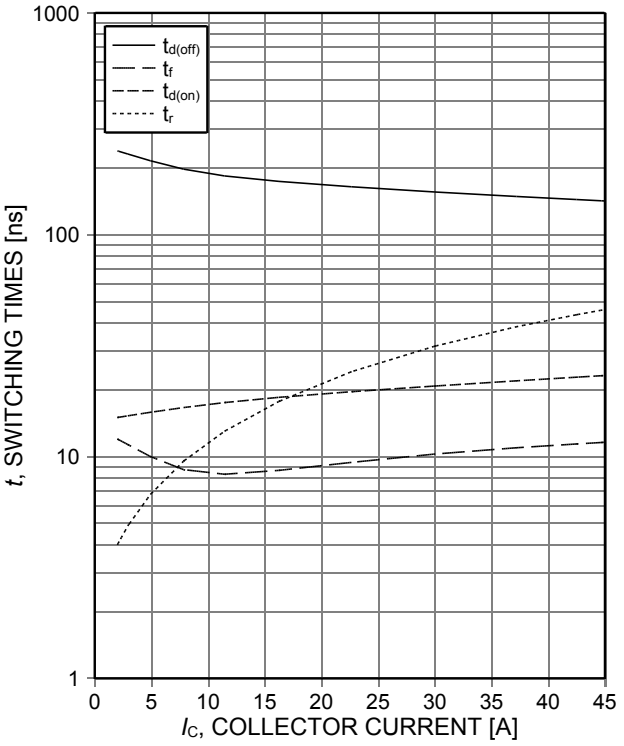


Figure 8. **Typical switching times as a function of collector current**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, r_G=39Ω, Dynamic test circuit in Figure E)

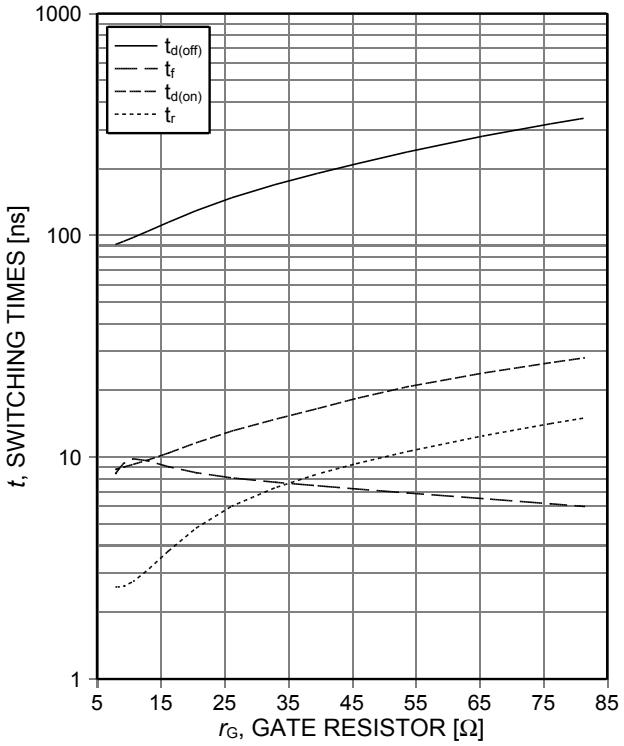


Figure 9. **Typical switching times as a function of gate resistor**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, I_C=7,5A,Dynamic test circuit in Figure E)

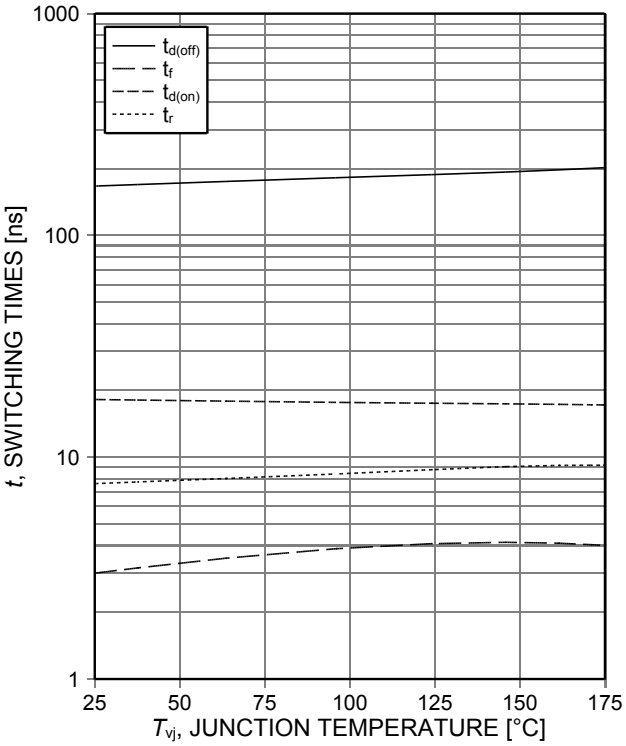


Figure 10. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=7,5A, r_G=39Ω,Dynamic test circuit in Figure E)

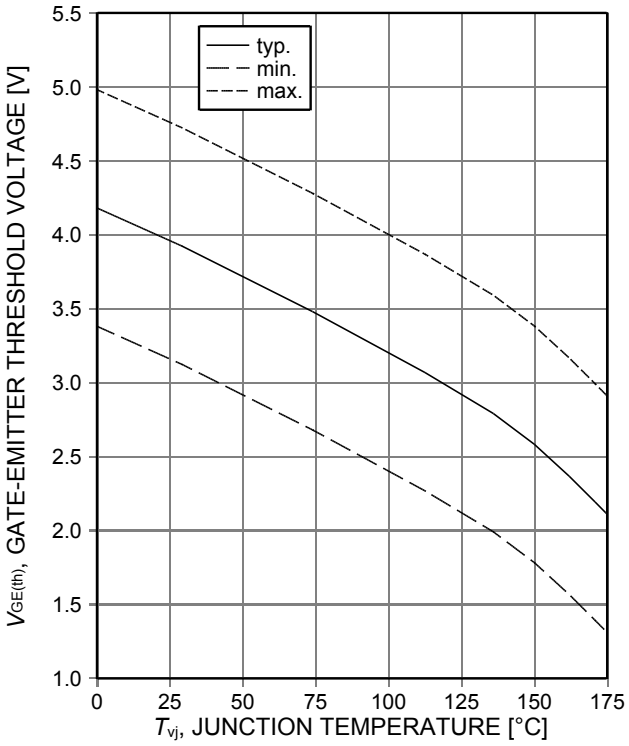


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0.15mA)

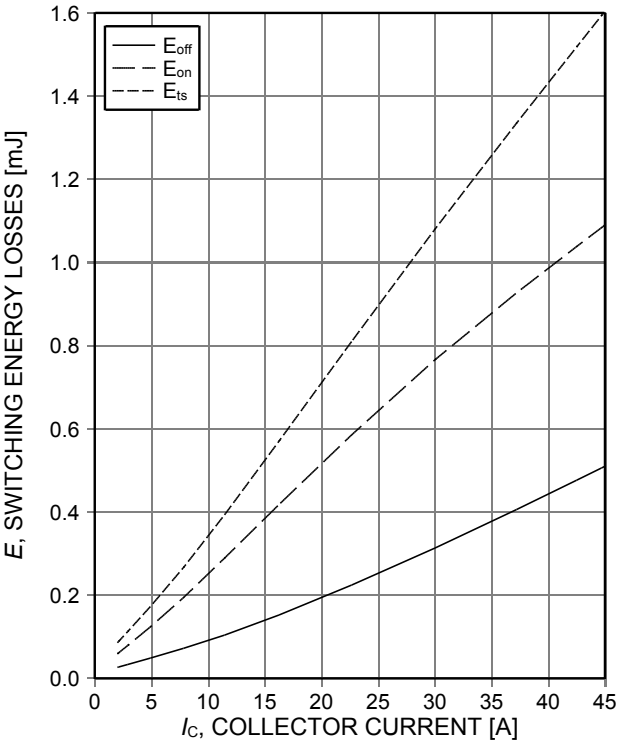


Figure 12. **Typical switching energy losses as a function of collector current**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, r_G=39Ω,Dynamic test circuit in Figure E)

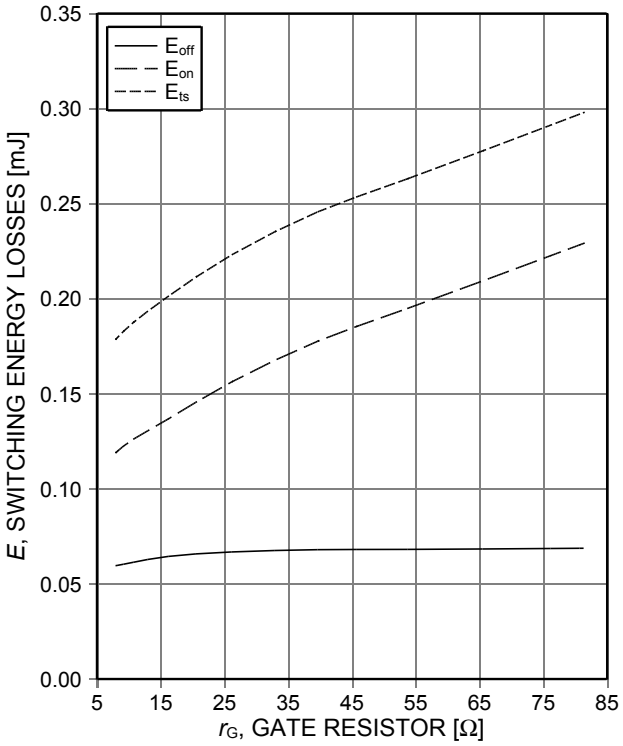


Figure 13. **Typical switching energy losses as a function of gate resistor** (inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, I_C=7,5A, Dynamic test circuit in Figure E)

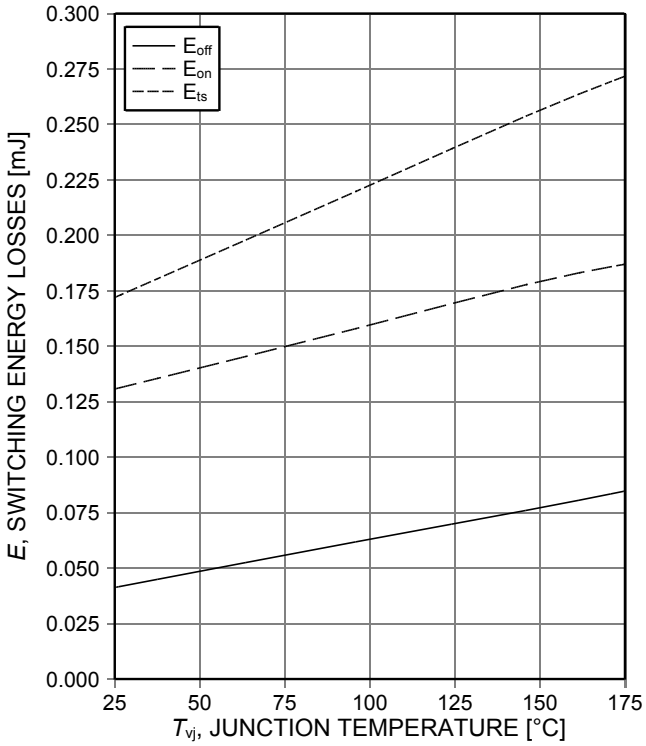


Figure 14. **Typical switching energy losses as a function of junction temperature** (inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=7,5A, r_G=39Ω,Dynamic test circuit in Figure E)

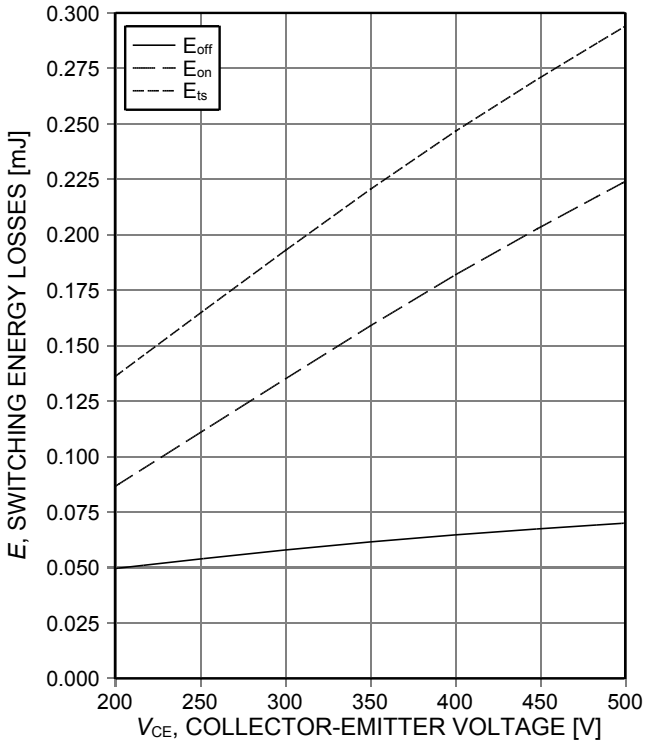


Figure 15. **Typical switching energy losses as a function of collector emitter voltage** (inductive load, T_{vj}=150°C, V_{GE}=15/0V, I_C=7,5A, r_G=39Ω,Dynamic test circuit in Figure E)

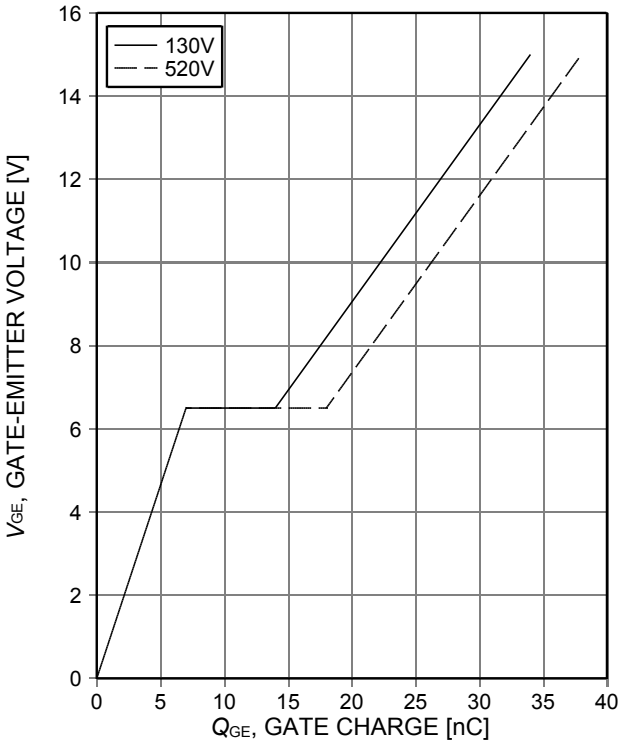


Figure 16. **Typical gate charge** (I_C=15A)

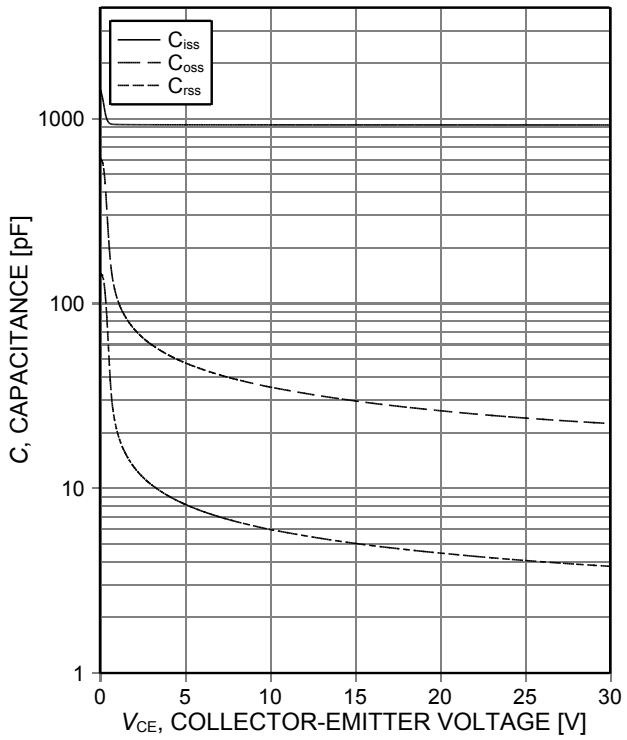


Figure 17. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

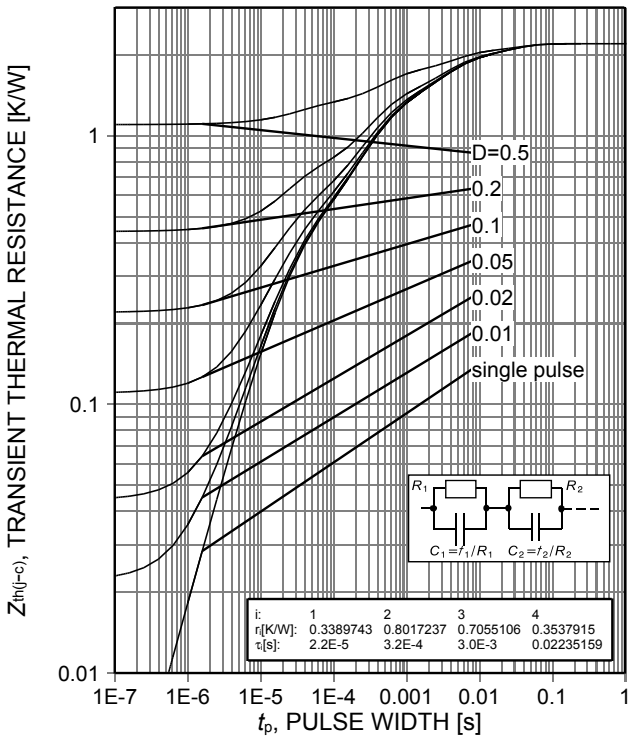


Figure 18. **IGBT transient thermal resistance**
($D=t_p/T$)

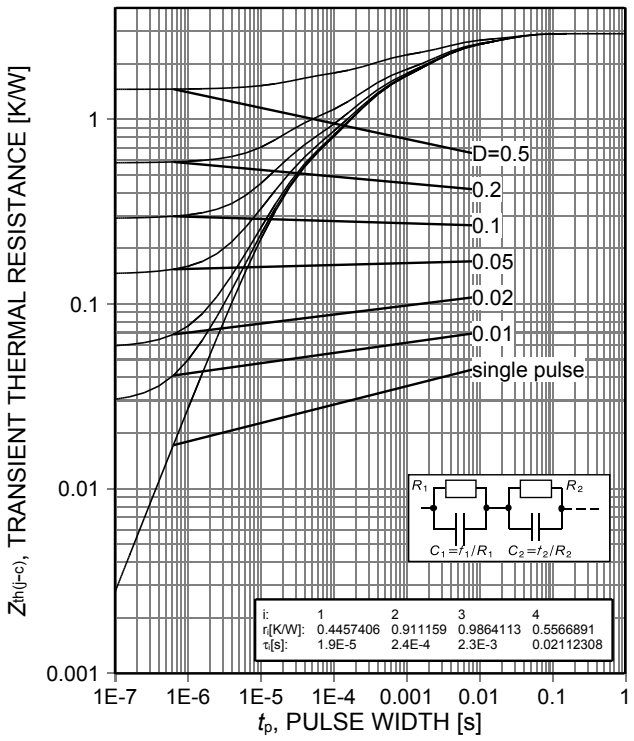


Figure 19. **Diode transient thermal impedance as a function of pulse width**
($D=t_p/T$)

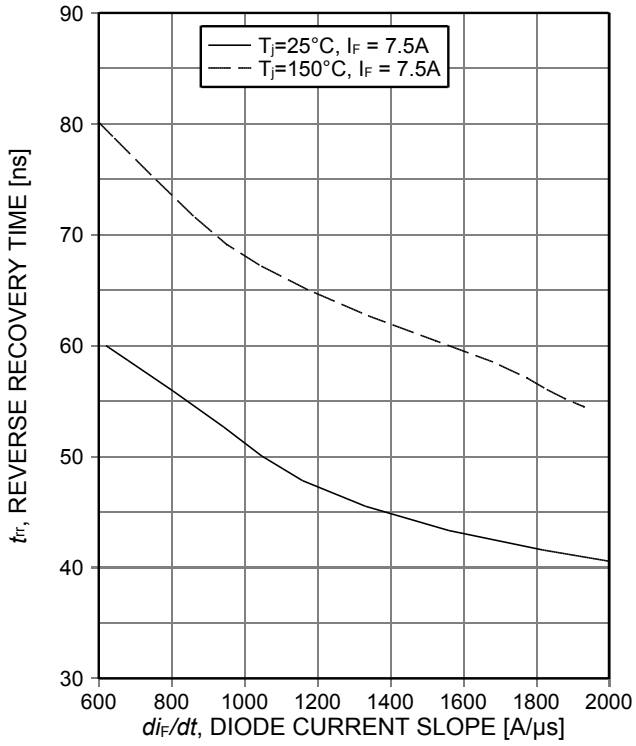


Figure 20. **Typical reverse recovery time as a function of diode current slope**
(V_R=400V)

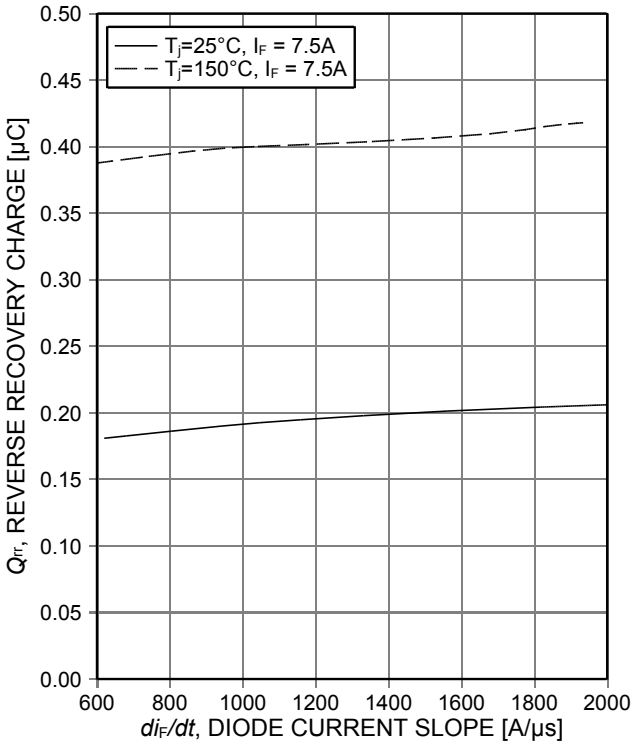


Figure 21. **Typical reverse recovery charge as a function of diode current slope** (V_R=400V)

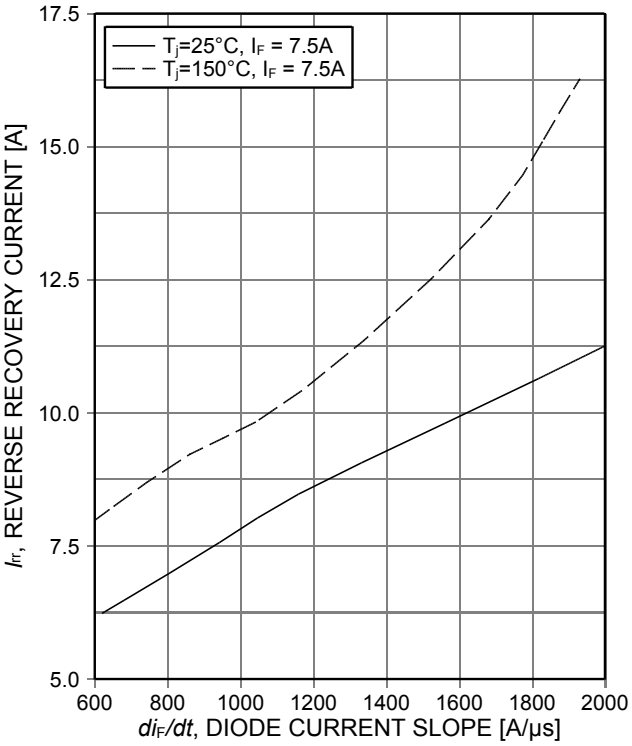


Figure 22. **Typical reverse recovery current as a function of diode current slope** (V_R=400V)

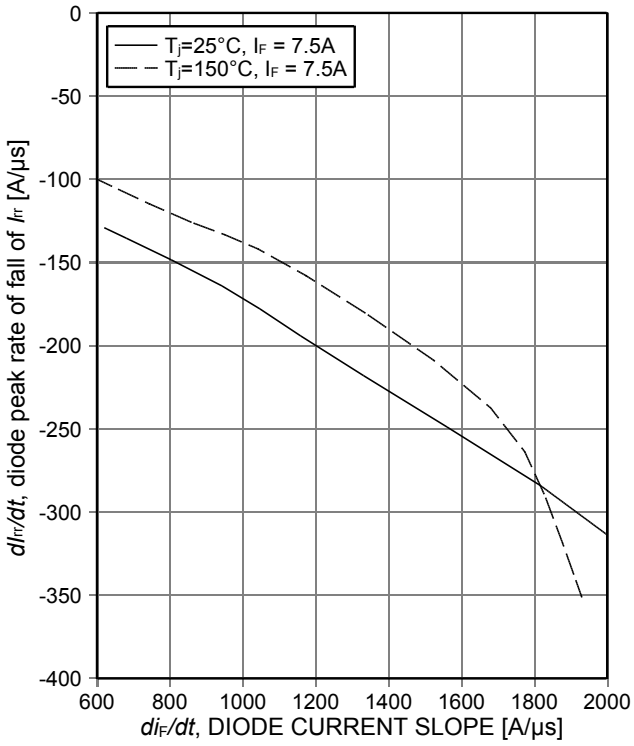


Figure 23. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope** (V_R=400V)

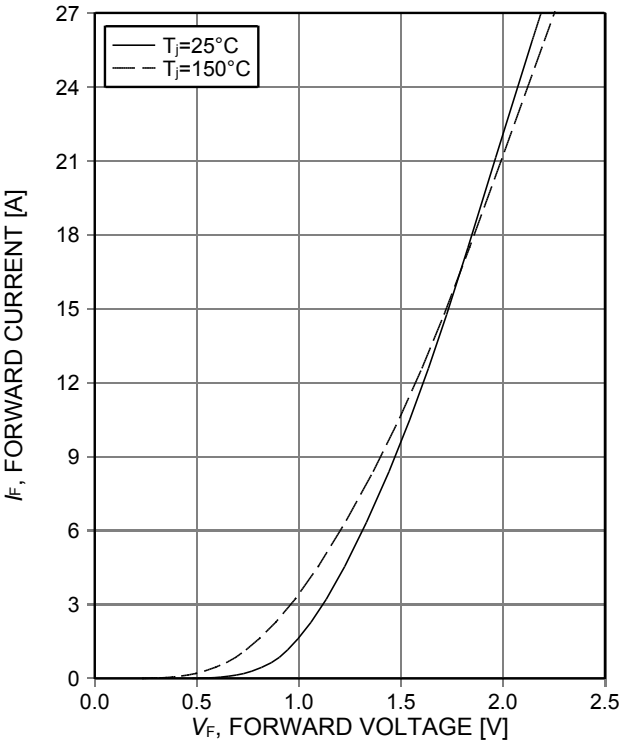


Figure 24. **Typical diode forward current as a function of forward voltage**

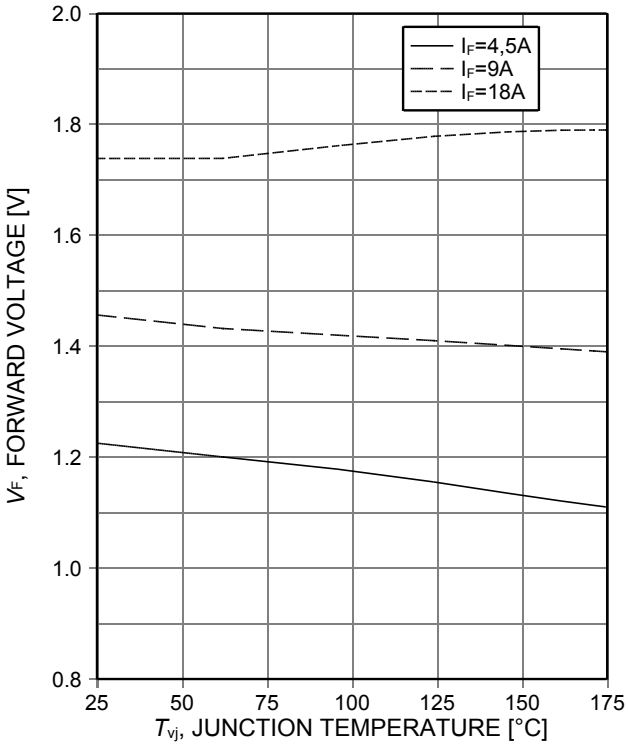
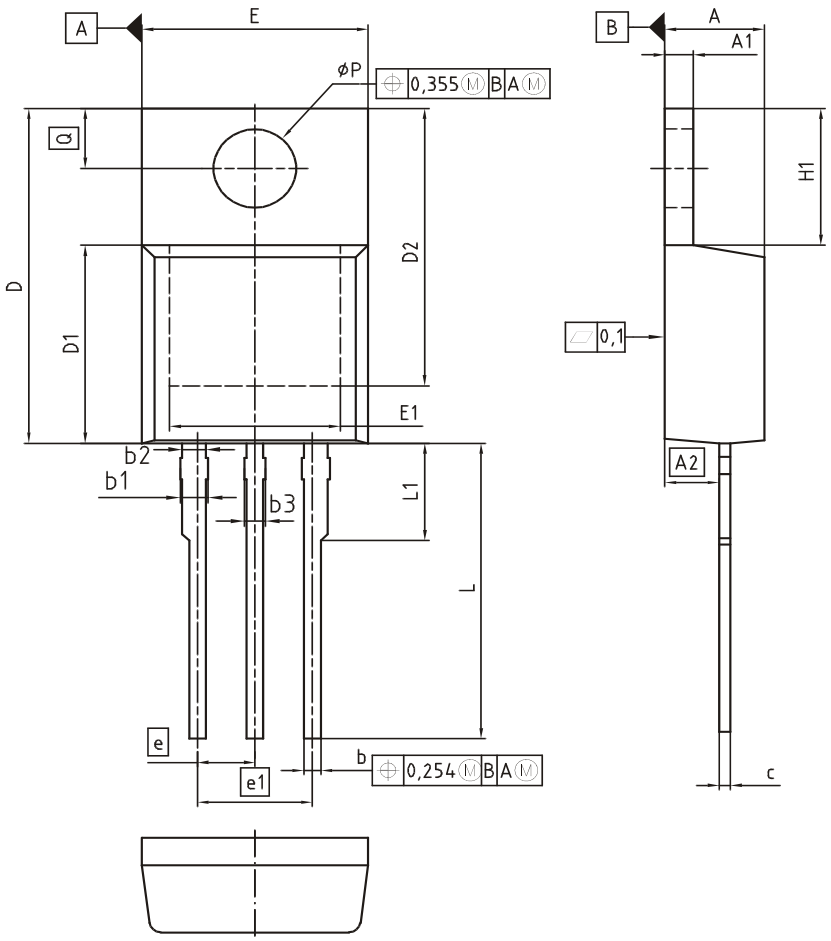


Figure 25. **Typical diode forward voltage as a function of junction temperature**

Package Drawing PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

SCALE 0 2.5 0 2.5 5mm

EUROPEAN PROJECTION

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REVISION
06

Testing Conditions

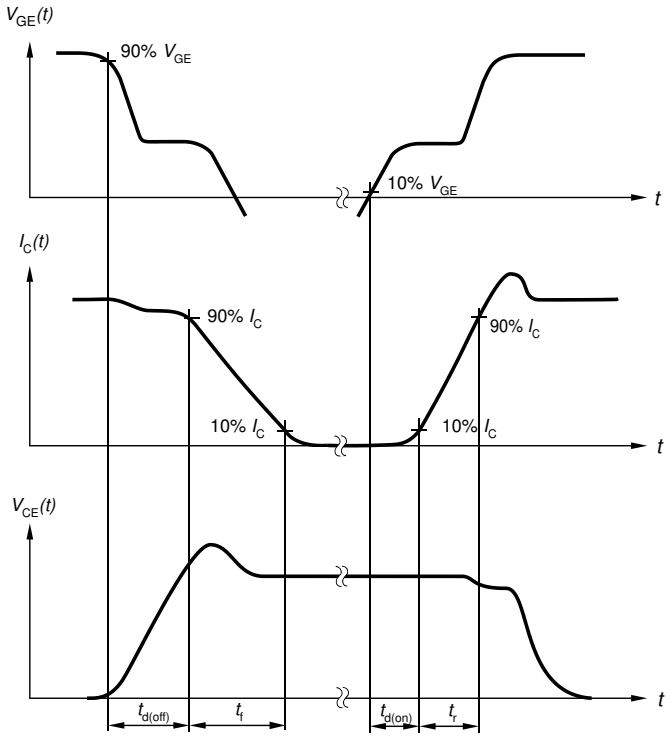

Figure A. **Definition of switching times**

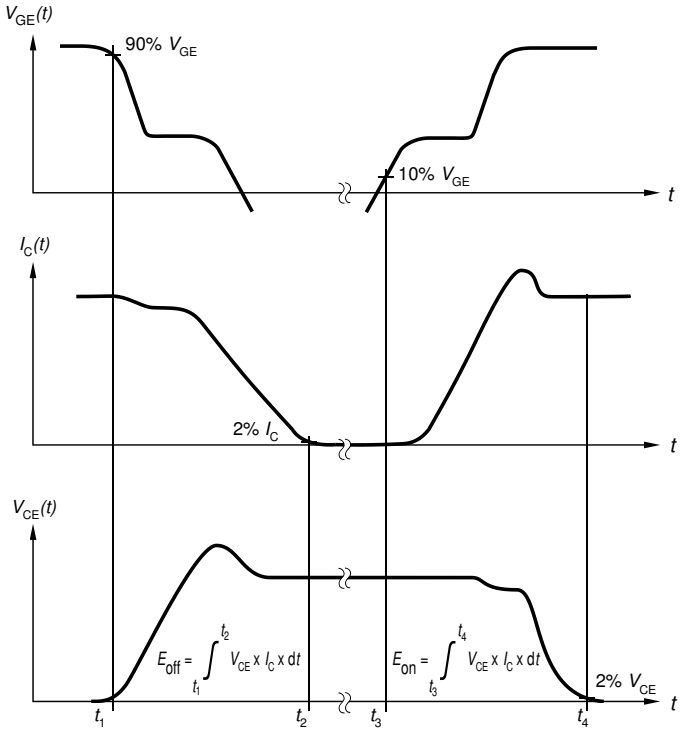

Figure B. **Definition of switching losses**

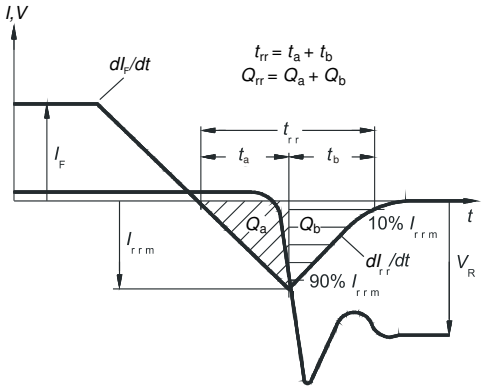

Figure C. **Definition of diode switching characteristics**

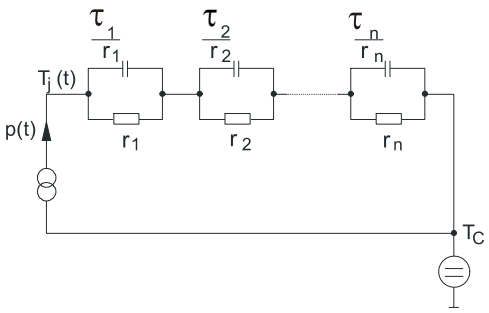

Figure D. **Thermal equivalent circuit**

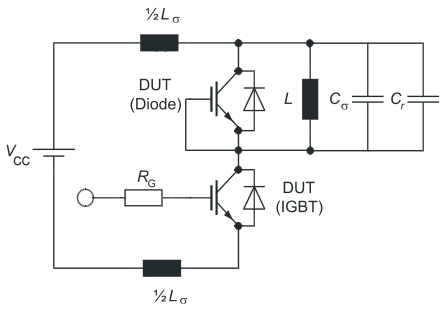

Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

Revision History

IKP15N65F5

Revision: 2015-05-05, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.1	2012-11-09	Preliminary data sheet
1.2	2013-12-18	New Marking Pattern
2.1	2015-05-05	Final data sheet

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